



## STB70NFS03L

N-channel - 30V - 0.0075Ω - 70A D<sup>2</sup>PAK  
STriP<sup>2</sup>FET™ Power MOSFET plus schottky rectifier

### General features

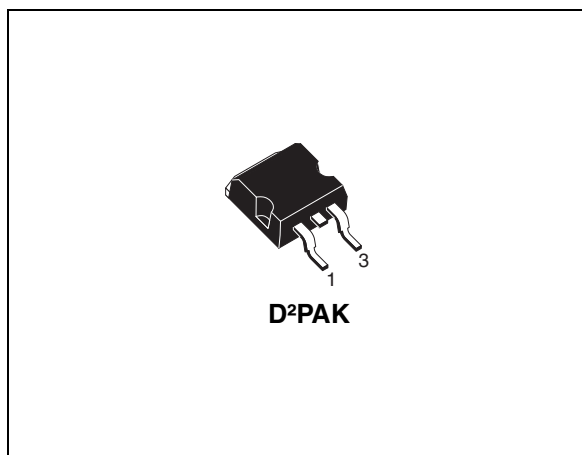
Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB70NFS03L	30V	<0.0095Ω	70A
Schottky	I <sub>F(AV)</sub>	V <sub>RRM</sub>	V <sub>F(MAX)</sub>
	3A	30V	0.51V

### Description

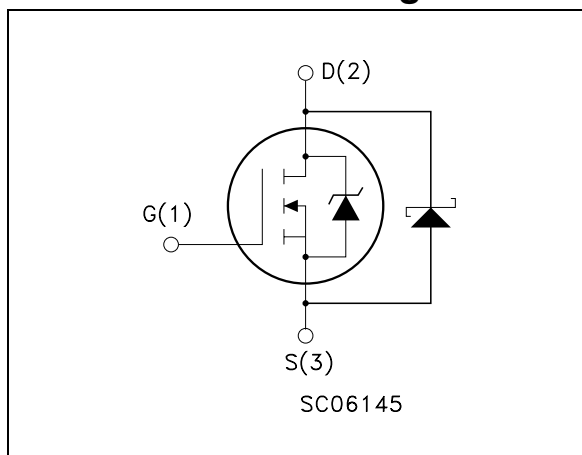
This product associates a Power MOSFET of the third generation of STMicroelectronics unique “Single Feature Size” strip-based process and a low drop schottky diode. The transistor shows the best trade-off between on-resistance and gate charge. Used as low side in buck regulators, the product is the solution in terms of conduction losses and space saving.

### Applications

- Switching application



### Internal schematic diagram



### Order codes

Part number	Marking	Package	Packaging
STB70NFS03L	B70NFS03L	D <sup>2</sup> PAK	Tape & reel

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
	2.1 Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>8</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>9</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>11</b>
<b>6</b>	<b>Revision history</b> .....	<b>12</b>

# 1 Electrical ratings

**Table 1. Mosfet absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate- source voltage	$\pm 18$	V
$I_D$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	70	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	50	A
$I_{DM}^{(1)}$	Drain current (pulsed)	280	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	100	W
	Derating factor	0.67	W/ $^\circ\text{C}$
$dv/dt^{(2)}$	Peak diode recovery voltage slope	5.5	V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	500	mJ
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_J$	Operating junction temperature		

1. Pulse width limited by safe operating area
2.  $I_{SD} \leq 70\text{A}$ ,  $di/dt \leq 350\text{A}/\mu\text{s}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$
3. Starting  $T_j = 25^\circ\text{C}$ ,  $V_{DD} = 25\text{V}$

**Table 2. Schottky absolute maximum ratings**

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		20	A
$I_{F(AV)}$	Average forward current	$T_L=125^\circ\text{C}$ $\delta=0.5$	3	A
$I_{FSM}$	Surge non repetitive forward current	$t_p=10\text{ms}$ Sinusoidal	75	A
$dv/dt$	Critical rate of rise of reverse voltage		10000	v/ $\mu\text{s}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-amb}$	Thermal resistance junction-amb max	1.5	$^\circ\text{C}/\text{W}$
$R_{thj-case}$	Thermal resistance junction-case max	62.5	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

## 2 Electrical characteristics

(T<sub>case</sub> = 25°C unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0	30			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max rating V <sub>DS</sub> = Max rating, T <sub>C</sub> = 125°C			200 20	μA mA
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 18V			± 100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1			V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 35A V <sub>GS</sub> = 5V, I <sub>D</sub> = 18A		0.0075 0.0135	0.0095 0.018	Ω Ω

**Table 5. Shottcky static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I <sub>R</sub>	Reverse leakage current	T <sub>j</sub> = 25°C V <sub>R</sub> = 30V T <sub>j</sub> = 100°C V <sub>R</sub> = 30V		0.03	0.2 100	mA mA
V <sub>F</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	T <sub>j</sub> = 25°C I <sub>F</sub> = 3A T <sub>j</sub> = 125°C I <sub>F</sub> = 3A		0.425	0.51 0.46	V V

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub>	Forward transconductance	V <sub>DS</sub> = 25V, I <sub>D</sub> = 35A		25		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	V <sub>DS</sub> = 25 V, f = 1 MHz, V <sub>GS</sub> = 0		1440 560 135		pF pF pF
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	V <sub>DD</sub> = 15V, I <sub>D</sub> = 70A, V <sub>GS</sub> = 5V (see <a href="#">Figure 11</a> )		22.5 9 12	30	nC nC nC

**Table 7. Switching times**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 15V$ , $I_D = 35A$ , $R_G = 4.7\Omega$ , $V_{GS} = 5V$ (see <a href="#">Figure 10</a> )		22 165		ns ns
$t_{d(off)}$ $t_f$	Turn-off delay time Fall time	$V_{DD} = 15V$ , $I_D = 35A$ , $R_G = 4.7\Omega$ , $V_{GS} = 5V$ (see <a href="#">Figure 10</a> )		21 25		ns ns

**Table 8. Source drain diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				70	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				280	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 70A$ , $V_{GS} = 0$			1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 70A$ , $di/dt = 100A/\mu s$		42		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 20V$ , $T_j = 150^\circ C$		52		nC
$I_{RRM}$	Reverse recovery current	(see <a href="#">Figure 15</a> )		2.5		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %

## 2.1 Electrical characteristics (curves)

Figure 1. Output characteristics

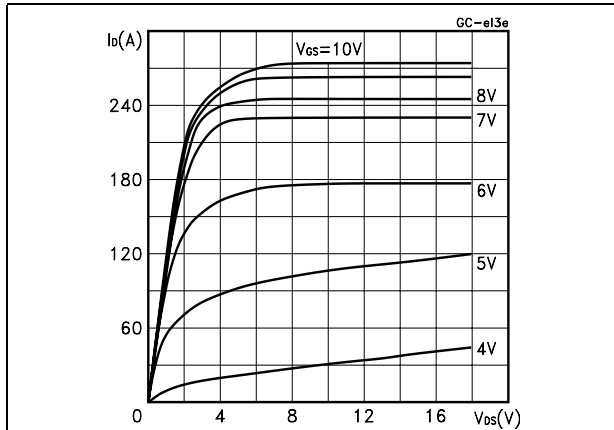


Figure 2. Transfer characteristics

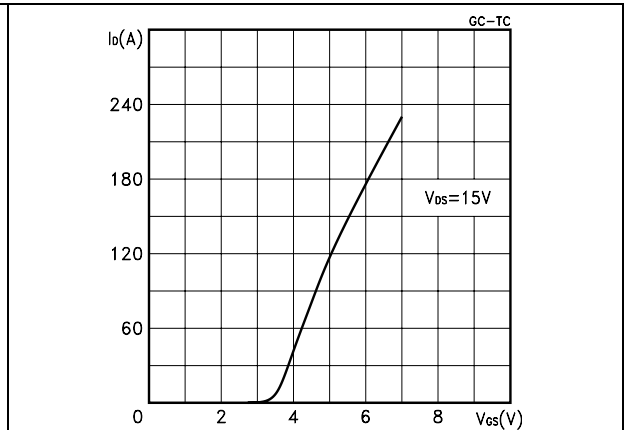


Figure 3. Source-drain diode forward characteristics

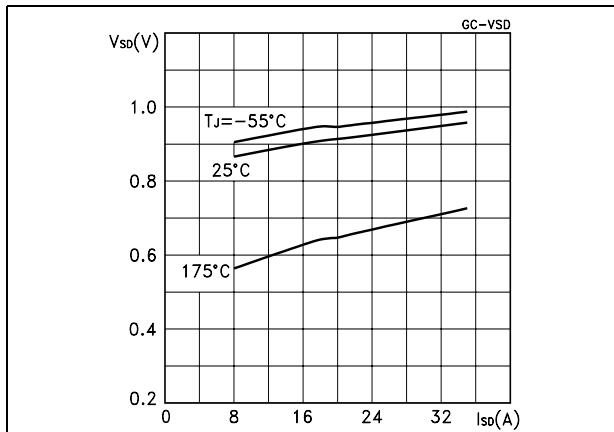


Figure 4. Static drain-source on resistance

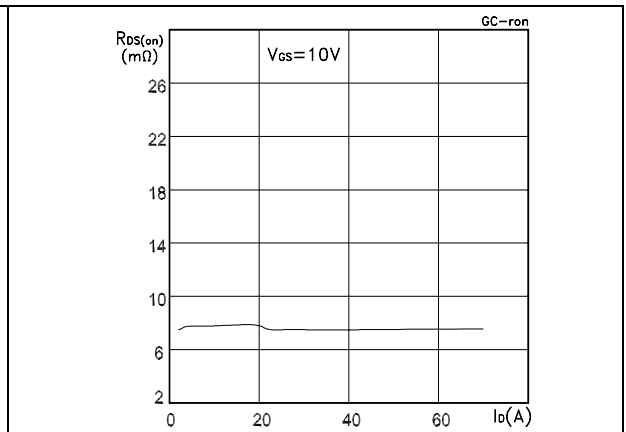


Figure 5. Gate charge vs gate-source voltage

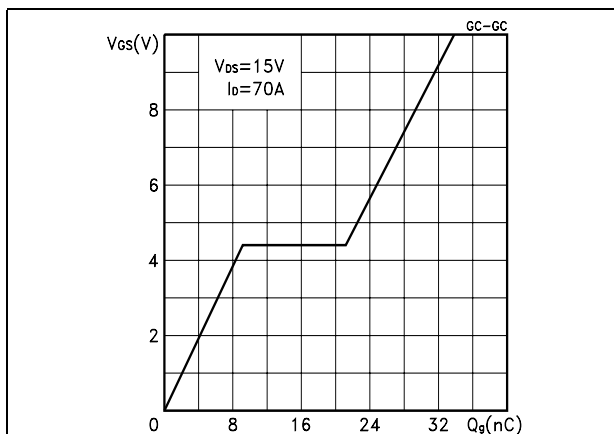


Figure 6. Capacitance variations

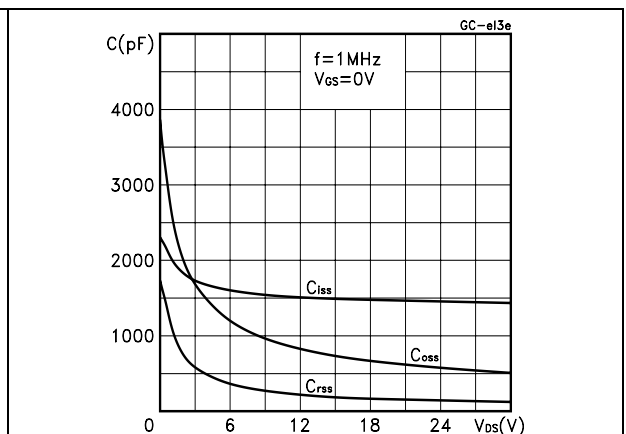


Figure 7. Normalized gate threshold voltage vs temperature

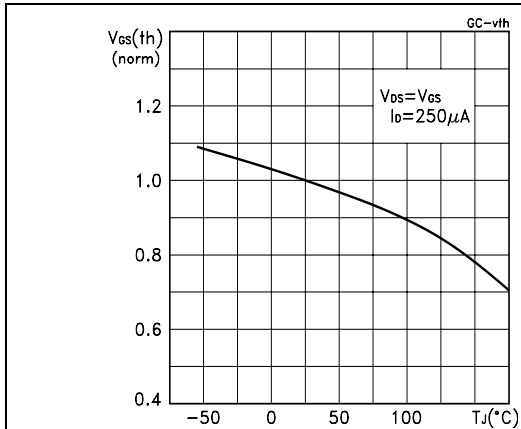


Figure 8. Normalized on resistance vs temperature

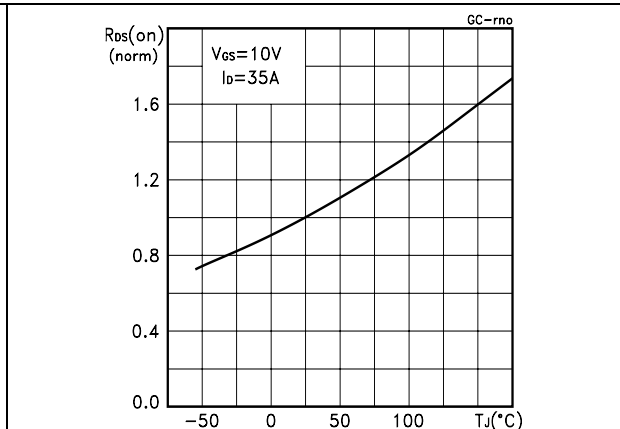
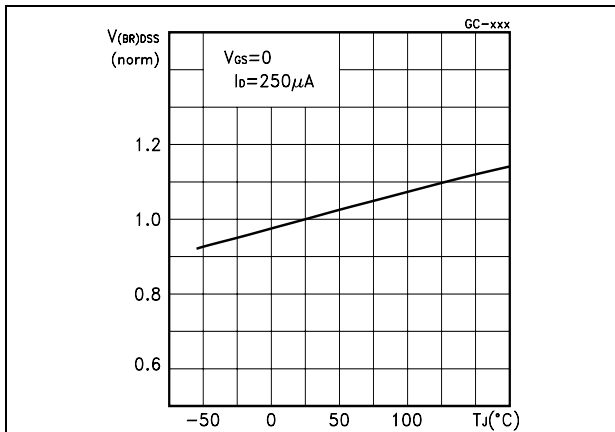


Figure 9. Normalized  $BV_{DSS}$  voltage vs temperature



### 3 Test circuits

Figure 10. Switching times test circuit for resistive load

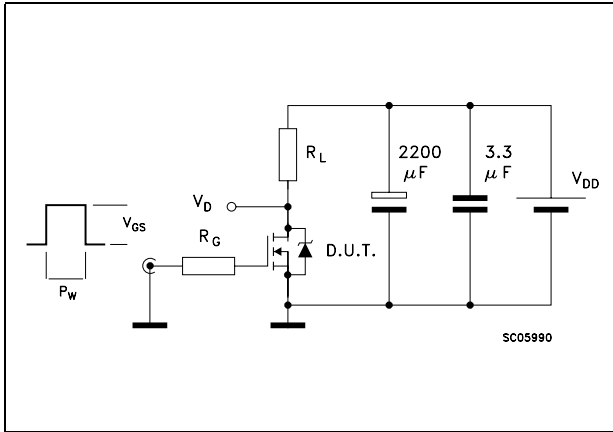


Figure 11. Gate charge test circuit

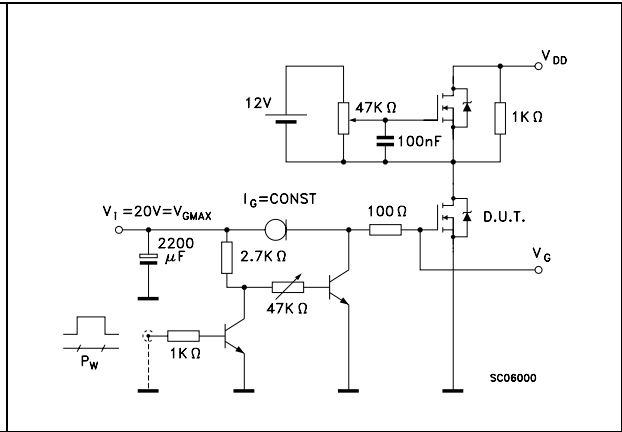


Figure 12. Test circuit for inductive load switching and diode recovery times

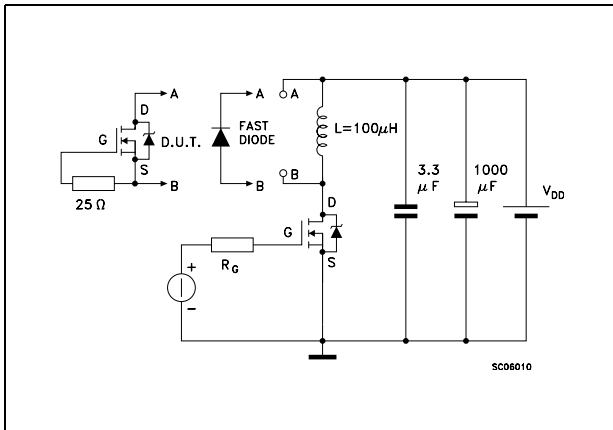


Figure 13. Unclamped inductive load test circuit

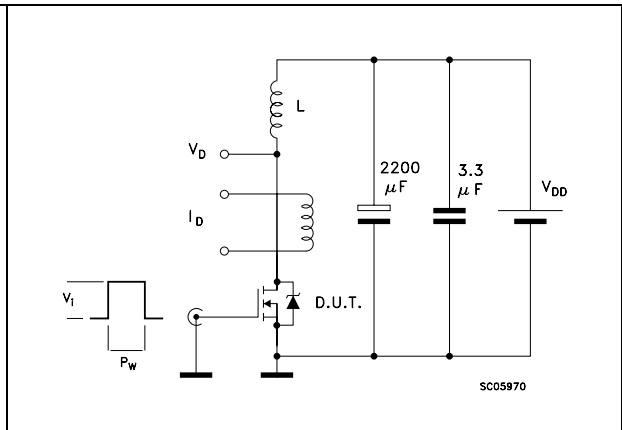
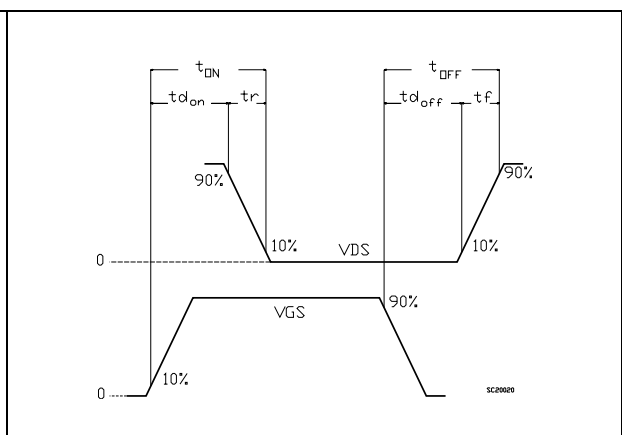


Figure 14. Unclamped inductive waveform



Figure 15. Switching time waveform



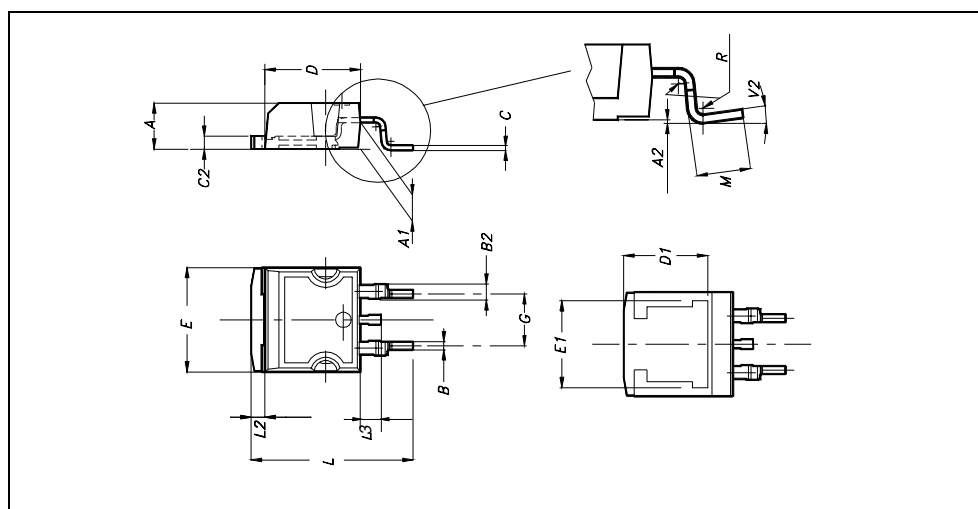


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

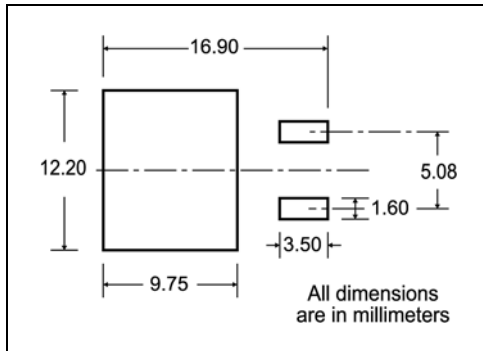
**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

\* on sales type

## 6 Revision history

**Table 9. Revision history**

Date	Revision	Changes
09-Sep-2004	8	New datasheet according to PCN DSG/CT/2C13 marking: STB70NFS03L@
05-Jul-2006	9	New template, new value on <a href="#">Table 4.:</a> <i>On /off states</i>

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